



AMERICAN  
MICROSEMICONDUCTOR

# 2N915 Transistors

Si NPN LP HF BJT

Military/High-Rel N

$V_{(BR)CEO}$  (V) 50

$V_{(BR)CBO}$  (V) 70

$I_C$  Max. (A)

Absolute Max. Power Diss. (W) 360m

Maximum Operating Temp ( $\theta C$ ) 200 $\phi$

$I_{CBO}$  Max. (A) 10n

@ $V_{CBO}$  (V) (Test Condition) 60

$h_{FE}$  Min. Current gain. 50

$h_{FE}$  Max. Current gain. 200

@ $I_C$  (A) (Test Condition) 10m

@ $V_{CE}$  (V) (Test Condition) 5.0

$f_T$  Min. (Hz) Transition Freq

@ $I_C$  (A) (Test Condition)

@ $V_{CE}$  (V) (Test Condition)

$V_{CEsat}$  Max. (V) 1.0

@ $I_C$  (A) (Test Condition) 10m

@ $I_B$  (A) (Test Condition) 1.0m

$h_{fe}$  Min. SS Current gain. 2.5

@ $I_C$  (A) (Test Condition) 10m

@ $V_{CE}$  (V) (Test Condition) 15